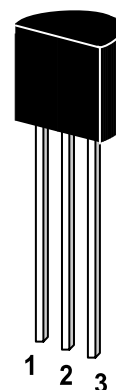


NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.

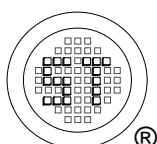


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

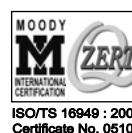
Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^{\circ}\text{C}$



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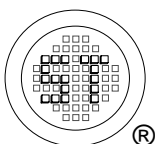
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listed on the Hong Kong Stock Exchange, Stock Code: 724)



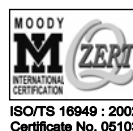
Dated : 07/12/2002

Characteristics at $T_{amb}=25^{\circ}C$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6V$, $I_C=1mA$					
Current Gain Group R	h_{FE}	90	-	180	-
O	h_{FE}	135	-	270	-
Y	h_{FE}	200	-	400	-
G	h_{FE}	300	-	600	-
Collector Base Breakdown Voltage at $I_C=100\mu A$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10mA$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu A$	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $V_{CB}=60V$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=5V$	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=100mA$, $I_B=10mA$	$V_{CE(sat)}$	-	0.15	0.3	V
Base Saturation Voltage at $I_C=100mA$, $I_B=10mA$	$V_{BE(sat)}$	-	0.86	1	V
Gain Bandwidth Product at $V_{CE}=6V$, $I_C=10mA$	f_T	-	250	-	MHz
Output Capacitance at $V_{CB}=6V$, $f=1MHz$	C_{OB}	-	3	-	pF



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